

## General Description

The 12P04D uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as -4.5V. This device is suitable for use as a wide variety of applications.



## Features

$V_{DS} = -40V, I_D = -12A$

**TO252-2L**

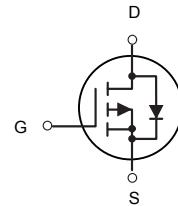
$R_{DS(ON)} < 36m\Omega @ V_{GS} = -10V$

$R_{DS(ON)} < 52m\Omega @ V_{GS} = -4.5V$

High Power and current handing capability

Lead free product is acquired

Surface Mount Package



P-Channel MOSFET

## Application

PWM applications

Load switch

Power management

## Absolute Maximum Ratings ( $T_A=25^\circ C$ )

| Symbol                 | Parameter  | Value      | Unit |
|------------------------|--|------------|------|
| $V_{DS}$               | Drain-Source Voltage ( $V_{GS}=0V$ )                 | -40        | V    |
| $V_{GS}$               | Gate-Source Voltage ( $V_{DS}=0V$ )                  | $\pm 20$   | V    |
| $I_D$                  | Drain Current-Continuous( $T_c=25^\circ C$ )         | -12        | A    |
|                        | Drain Current-Continuous( $T_c=100^\circ C$ )        | -10        | A    |
| $I_{DM(\text{pulse})}$ | (Note 1)<br>Drain Current-Continuous@ Current-Pulsed | -80        | A    |
| $P_D$                  | Maximum Power Dissipation( $T_c=25^\circ C$ )        | 37.5       | W    |
|                        | Maximum Power Dissipation( $T_c=100^\circ C$ )       | 19         | W    |
| $T_J, T_{STG}$         | Operating Junction and Storage Temperature Range     | -55 To 175 | °C   |

|                 |                                     |   |      |
|-----------------|-------------------------------------|---|------|
| R <sub>JC</sub> | Thermal Resistance,Junction-to-Case | 4 | °C/W |
|-----------------|-------------------------------------|---|------|

**Electrical Characteristics (TA=25°C unless otherwise noted)**

| Symbol                | Parameter                        | Conditions   | Min | Typ | Max  | Unit |
|-----------------------|----------------------------------|--|-----|-----|------|------|
| BV <sub>DSS</sub>     | Drain-Source Breakdown Voltage   | V <sub>GS</sub> =0V I <sub>D</sub> =-250μA   | -40 |     |      | V    |
| I <sub>DSS</sub>      | Zero Gate Voltage Drain Current  | V <sub>DS</sub> =-32V, V <sub>GS</sub> =0V   |     |     | -1   | μA   |
| I <sub>GSS</sub>      | Gate-Body Leakage Current        | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V   |     |     | ±100 | nA   |
| V <sub>GS(th)</sub>   | Gate Threshold Voltage           | V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA                              | -1  | -2  | -3   | V    |
| g <sub>FS</sub>       | Forward Transconductance         | V <sub>DS</sub> =-5V, I <sub>D</sub> =-10A   |     | 25  |      | S    |
| R <sub>D(S(ON))</sub> | Drain-Source On-State Resistance | V <sub>GS</sub> =-10V, I <sub>D</sub> =-20A  |     | 25  | 36   | mΩ   |
|                       |                                  | V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-10A   |     | 42  | 52   | mΩ   |
| C <sub>iss</sub>      | Input Capacitance                | V <sub>DS</sub> =-25V, V <sub>GS</sub> =0V, f=1.0MHz                                   |     | 840 |      | pF   |
| C <sub>oss</sub>      | Output Capacitance               |  |     | 92  |      | pF   |
| C <sub>rss</sub>      | Reverse Transfer Capacitance     |  |     | 60  |      | pF   |
| t <sub>d(on)</sub>    | Turn-on Delay Time               | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-20V, R <sub>L</sub> =1.6, R <sub>GEN</sub> =3 |     | 5   |      | nS   |
| t <sub>r</sub>        | Turn-on Rise Time                |  |     | 12  |      | nS   |
| t <sub>d(off)</sub>   | Turn-Off Delay Time              |  |     | 20  |      | nS   |
| t <sub>f</sub>        | Turn-Off Fall Time               |  |     | 4.5 |      | nS   |
| Q <sub>g</sub>        | Total Gate Charge                | V <sub>GS</sub> =-10V, V <sub>DS</sub> =-20V, I <sub>D</sub> =-15A                     |     | 20  |      | nC   |
| Q <sub>gs</sub>       | Gate-Source Charge               |  |     | 2.5 |      | nC   |
| Q <sub>gd</sub>       | Gate-Drain Charge                |  |     | 4.5 |      | nC   |
| I <sub>SD</sub>       | Source-Drain Current(Body Diode) |  |     |     | -20  | A    |
| V <sub>SD</sub>       | Forward on Voltage               | V <sub>GS</sub> =0V, I <sub>S</sub> =-20A  |     |     | -1.2 | V    |

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature

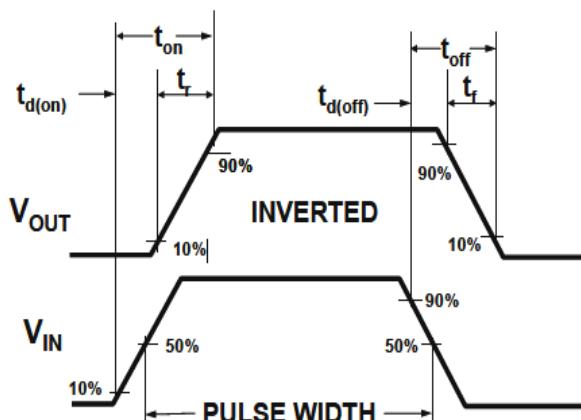
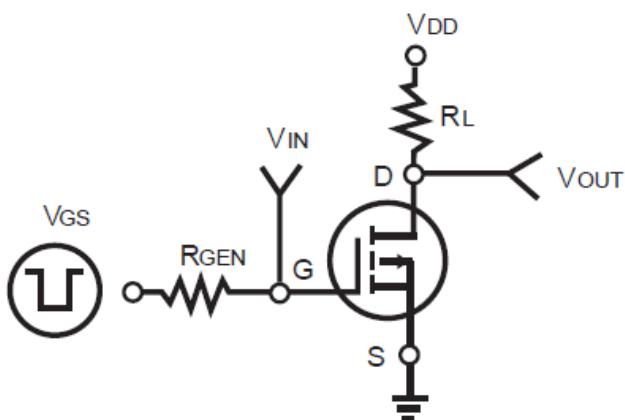
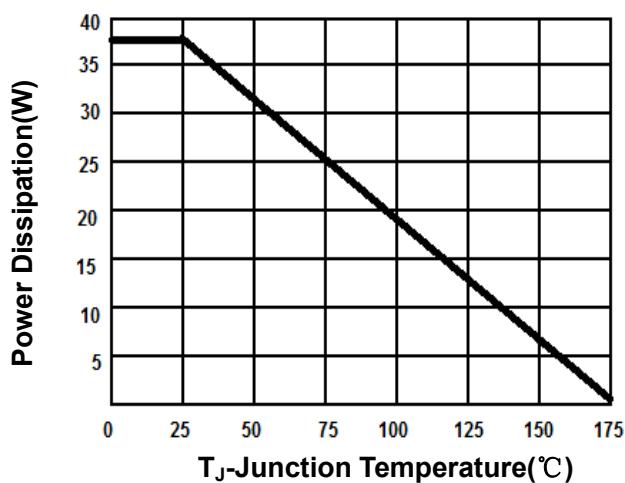
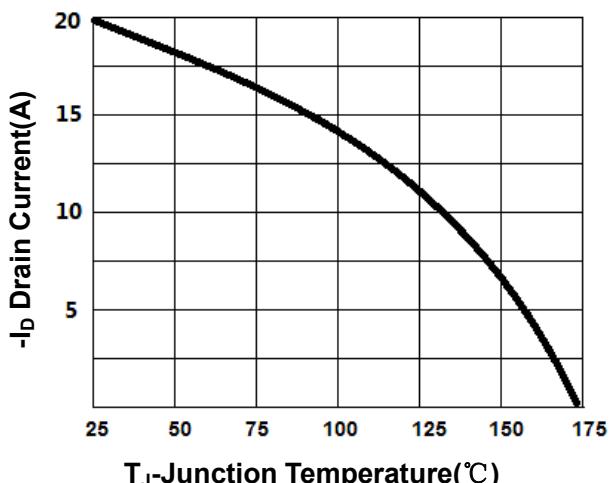
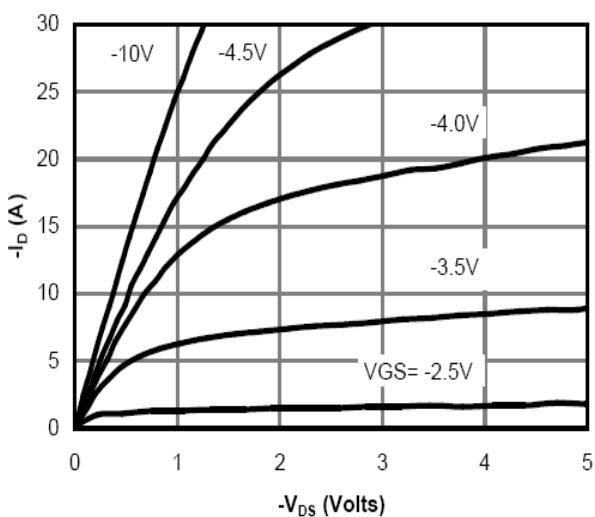
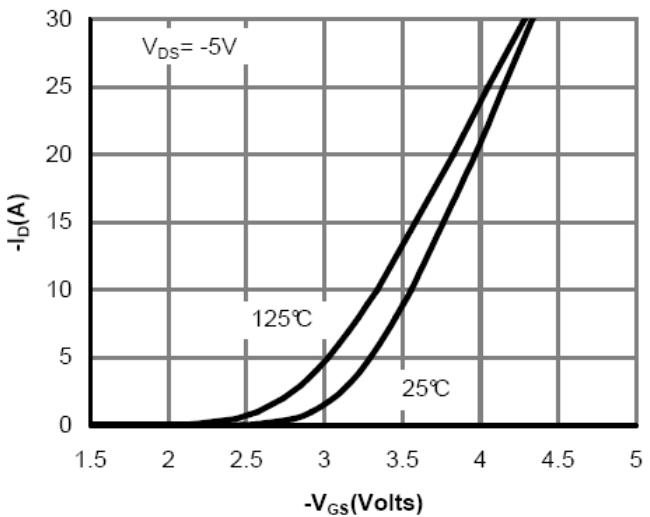
**Switch Time Test Circuit and Switching Waveforms:**

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (Curves)**
**Figure1. Power Dissipation**

**Figure2. Drain Current**

**Figure3. Output Characteristics**

**Figure4. Transfer Characteristics**


Figure5. Capacitance

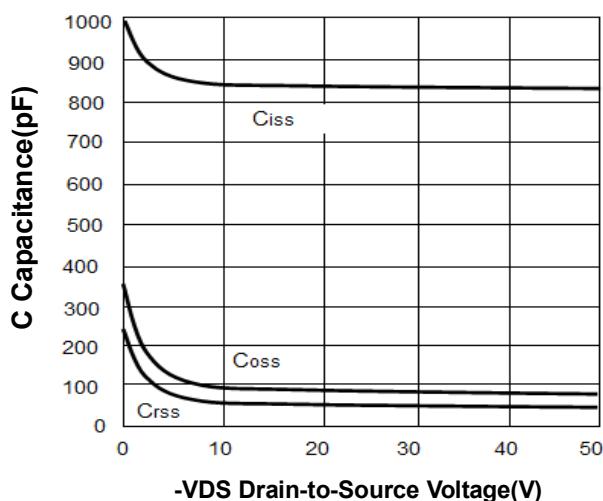
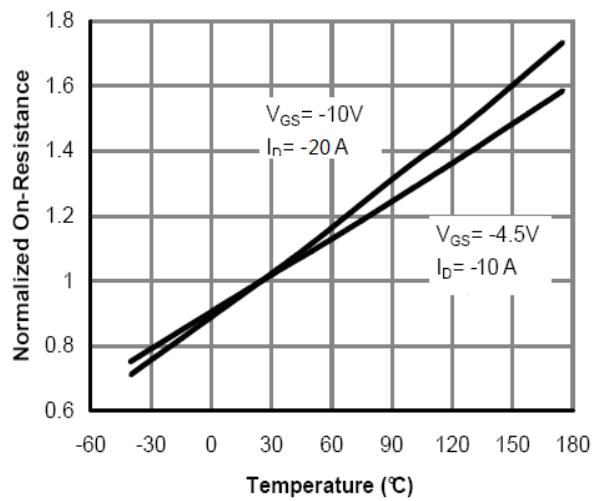
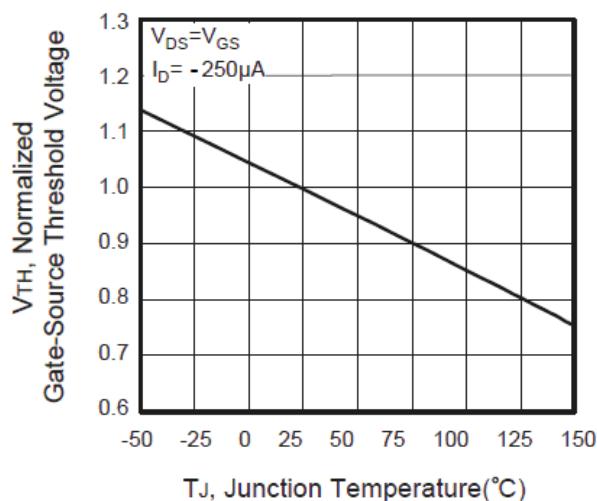

 Figure6.  $R_{DS(ON)}$  vs Junction Temperature

 Figure7.  $V_{GS(th)}$  vs Junction Temperature


Figure8. Gate Charge Waveforms

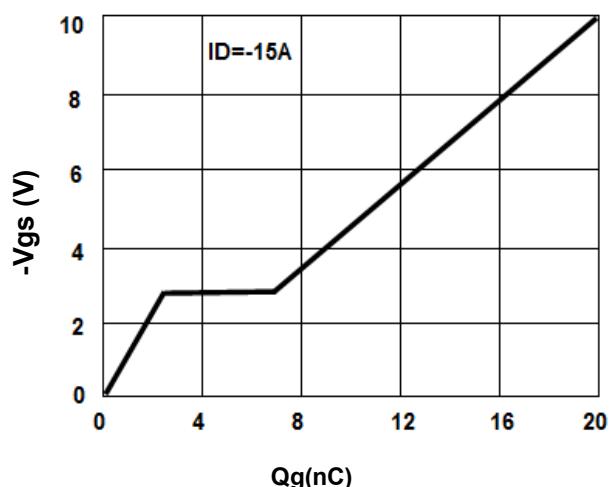
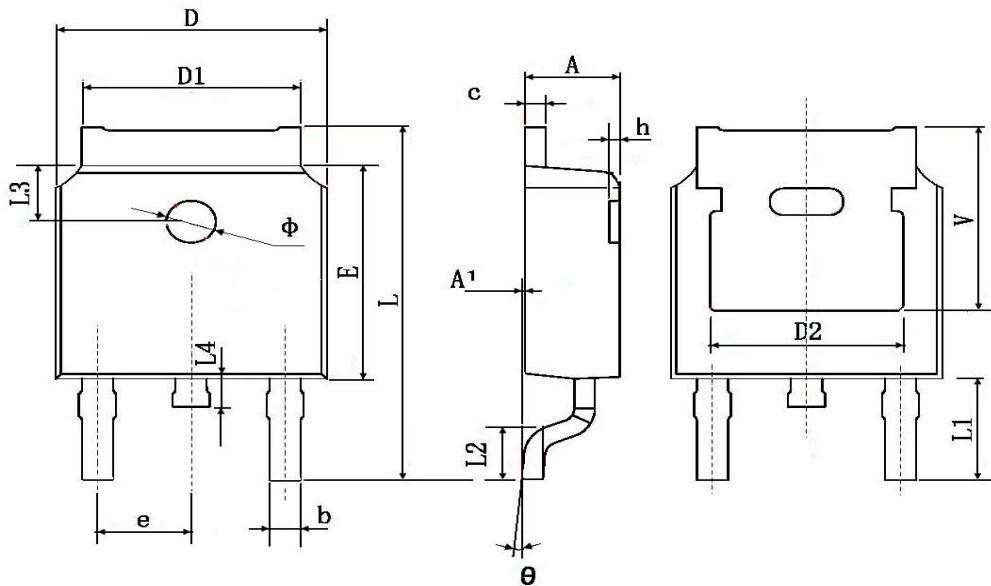


Figure9. Normalized Maximum Transient Thermal Impedance



## TO252-2L Package Information



| Symbol | Dimensions In Millimeters |        | Dimensions In Inches |       |
|--------|---------------------------|--------|----------------------|-------|
|        | Min.                      | Max.   | Min.                 | Max.  |
| A      | 2.200                     | 2.400  | 0.087                | 0.094 |
| A1     | 0.000                     | 0.127  | 0.000                | 0.005 |
| b      | 0.660                     | 0.860  | 0.026                | 0.034 |
| c      | 0.460                     | 0.580  | 0.018                | 0.023 |
| D      | 6.500                     | 6.700  | 0.256                | 0.264 |
| D1     | 5.100                     | 5.460  | 0.201                | 0.215 |
| D2     | 4.830 TYP.                |        | 0.190 TYP.           |       |
| E      | 6.000                     | 6.200  | 0.236                | 0.244 |
| e      | 2.186                     | 2.386  | 0.086                | 0.094 |
| L      | 9.800                     | 10.400 | 0.386                | 0.409 |
| L1     | 2.900 TYP.                |        | 0.114 TYP.           |       |
| L2     | 1.400                     | 1.700  | 0.055                | 0.067 |
| L3     | 1.600 TYP.                |        | 0.063 TYP.           |       |
| L4     | 0.600                     | 1.000  | 0.024                | 0.039 |
| Φ      | 1.100                     | 1.300  | 0.043                | 0.051 |
| θ      | 0°                        | 8°     | 0°                   | 8°    |
| h      | 0.000                     | 0.300  | 0.000                | 0.012 |
| V      | 5.350 TYP.                |        | 0.211 TYP.           |       |